

# RBA250N10CHPF-4UA02

100V – 250A – N-channel Power MOS FET

Application : Automotive

R07DS1488EJ0100

Rev.1.00

Jul. 08, 2020

## Description

The RBA250N10CHPF-4UA02 is N-channel MOS Field Effect Transistor designed for high current switching applications.

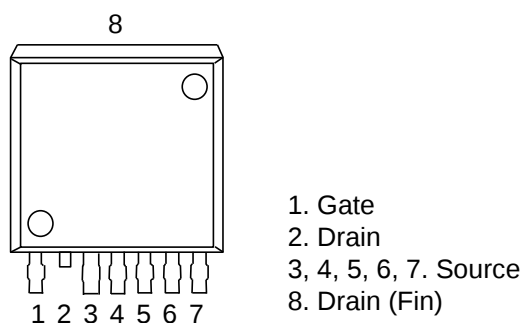
## Features

- Super low on-state resistance  
 $R_{DS(on)} = 2.4 \text{ m}\Omega \text{ MAX. ( } V_{GS} = 10 \text{ V, } I_D = 125\text{A )}$
- Low input capacitance  
 $C_{iss} = 9500\text{pF TYP. ( } V_{DS} = 50 \text{ V )}$
- Designed for automotive application and AEC-Q101 qualified
- Pb-free (This product does not contain Pb in the external electrode)

## Ordering Information

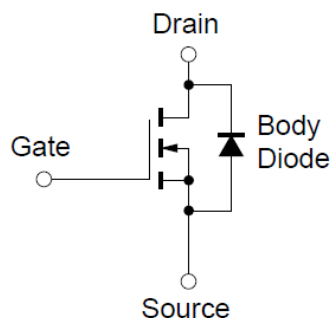
| Part No.                | Quantity    | Shipping container |
|-------------------------|-------------|--------------------|
| RBA250N10CHPF-4UA02#GB0 | 800pcs/reel | Taping             |

## Outline



TO-263-7pin-SHL\* (MP-25ZU)

\* Short Head & Lead



Equivalent circuit

**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

## Absolute Maximum Ratings

(T<sub>A</sub>=25°C)

| Item                                             | Symbol                | Ratings    | Unit |
|--------------------------------------------------|-----------------------|------------|------|
| Drain to Source Voltage (V <sub>GS</sub> = 0 V)  | V <sub>DSS</sub>      | 100        | V    |
| Gate to Source Voltage (V <sub>DS</sub> = 0 V)   | V <sub>GSS</sub>      | ±20        | V    |
| Drain Current (DC) (T <sub>C</sub> = 25 °C)      | I <sub>D(DC)</sub>    | ±250       | A    |
| Drain Current (pulse) <sup>Note1</sup>           | I <sub>D(pulse)</sub> | ±500       | A    |
| Total Power Dissipation (T <sub>C</sub> = 25 °C) | P <sub>T1</sub>       | 348        | W    |
| Total Power Dissipation (T <sub>A</sub> = 25 °C) | P <sub>T2</sub>       | 1.8        | W    |
| Channel Temperature                              | T <sub>ch</sub>       | 175        | °C   |
| Storage Temperature                              | T <sub>stg</sub>      | -55 to 175 | °C   |
| Avalanche Current <sup>Note2</sup>               | I <sub>AS</sub>       | 64         | A    |
| Avalanche Energy <sup>Note3</sup>                | E <sub>AS</sub>       | 409        | mJ   |

Note 1. P<sub>W</sub> ≤ 10 μs, Duty Cycle ≤ 1%2. V<sub>GS</sub> = 20 → 0V, R<sub>G</sub> = 25 Ω3. L = 100μH, V<sub>DD</sub> = 20V, V<sub>GS</sub> = 20 → 0V, R<sub>G</sub> = 25 Ω

## Thermal Resistance

|                                       |                       |      |      |
|---------------------------------------|-----------------------|------|------|
| Channel to Case Thermal Resistance    | R <sub>th(ch-C)</sub> | 0.43 | °C/W |
| Channel to Ambient Thermal Resistance | R <sub>th(ch-A)</sub> | 83.3 | °C/W |

## Electrical Characteristics

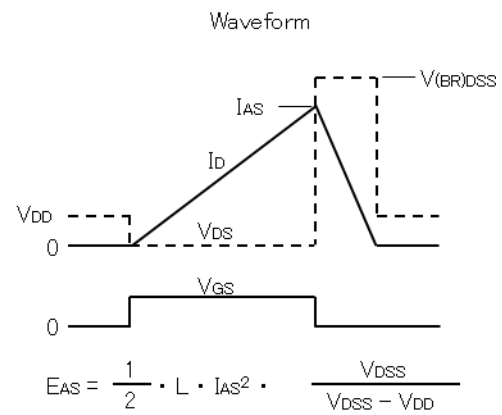
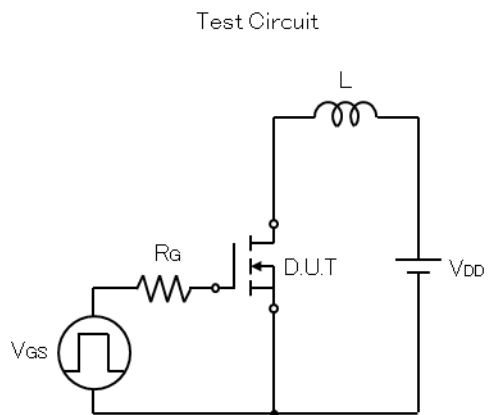
(T<sub>A</sub>=25°C)

| Item                                | Symbol                               | Min | Typ  | Max  | Unit | Test Conditions                                                                                  |
|-------------------------------------|--------------------------------------|-----|------|------|------|--------------------------------------------------------------------------------------------------|
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>                     |     |      | 10   | μA   | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V                                                   |
| Gate Leakage Current                | I <sub>GSS</sub>                     |     |      | ±100 | nA   | V <sub>GS</sub> = ± 20 V, V <sub>DS</sub> = 0 V                                                  |
| Gate to Source Threshold Voltage    | V <sub>GS(th)</sub>                  | 1.8 | 2.8  | 3.8  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                      |
| Drain to Source On-state Resistance | R <sub>DS(on)</sub> <sup>Note4</sup> |     | 1.9  | 2.4  | mΩ   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 125 A                                                   |
| Input Capacitance                   | C <sub>iss</sub>                     |     | 9500 |      | pF   | V <sub>DS</sub> = 50 V<br>V <sub>GS</sub> = 0 V<br>f = 1 MHz                                     |
| Output Capacitance                  | C <sub>oss</sub>                     |     | 460  |      | pF   |                                                                                                  |
| Reverse Transfer Capacitance        | C <sub>rss</sub>                     |     | 190  |      | pF   |                                                                                                  |
| Turn-on Delay Time                  | t <sub>d(on)</sub>                   |     | 30   |      | ns   | V <sub>DD</sub> = 50 V, I <sub>D</sub> = 125 A<br>V <sub>GS</sub> = 10 V<br>R <sub>G</sub> = 0 Ω |
| Rise Time                           | t <sub>r</sub>                       |     | 30   |      | ns   |                                                                                                  |
| Turn-off Delay Time                 | t <sub>d(off)</sub>                  |     | 130  |      | ns   |                                                                                                  |
| Fall Time                           | t <sub>f</sub>                       |     | 15   |      | ns   |                                                                                                  |
| Total Gate Charge                   | Q <sub>G</sub>                       |     | 190  |      | nC   | V <sub>DD</sub> = 80 V<br>V <sub>GS</sub> = 10 V<br>I <sub>D</sub> = 250A                        |
| Gate to Source Charge               | Q <sub>GS</sub>                      |     | 55   |      | nC   |                                                                                                  |
| Gate to Drain Charge                | Q <sub>GD</sub>                      |     | 50   |      | nC   |                                                                                                  |
| Body Diode Forward Voltage          | V <sub>F(S-D)</sub> <sup>Note4</sup> |     | 0.9  | 1.5  | V    | I <sub>F</sub> = 250 A, V <sub>GS</sub> = 0 V                                                    |
| Reverse Recovery Time               | t <sub>rr</sub>                      |     | 50   |      | ns   | I <sub>F</sub> = 250 A, V <sub>GS</sub> = 0 V                                                    |
| Reverse Recovery Charge             | Q <sub>rr</sub>                      |     | 85   |      | nC   | di/dt = 100 A/μs                                                                                 |

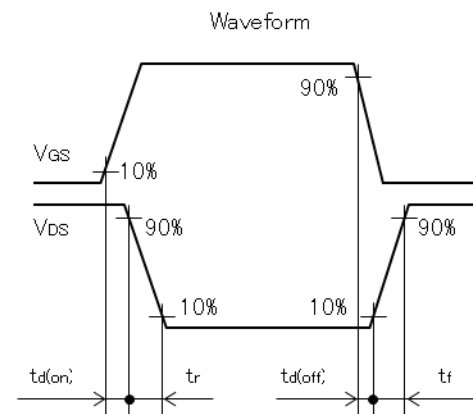
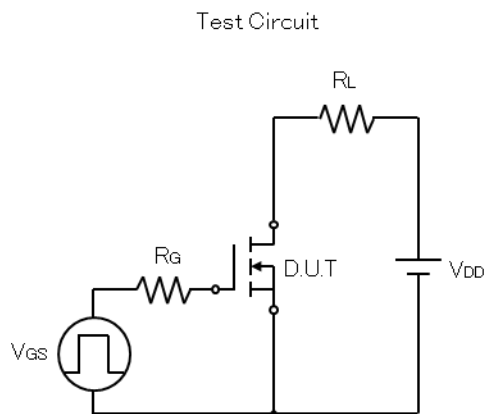
Note 4. Pulse test

## Test Circuit

### Avalanche

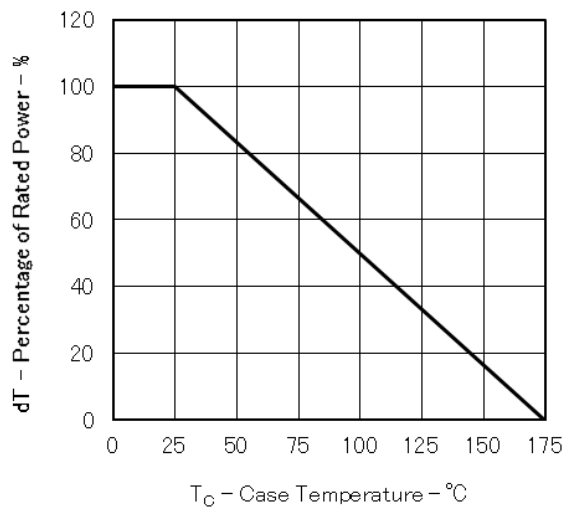


### Switching Time

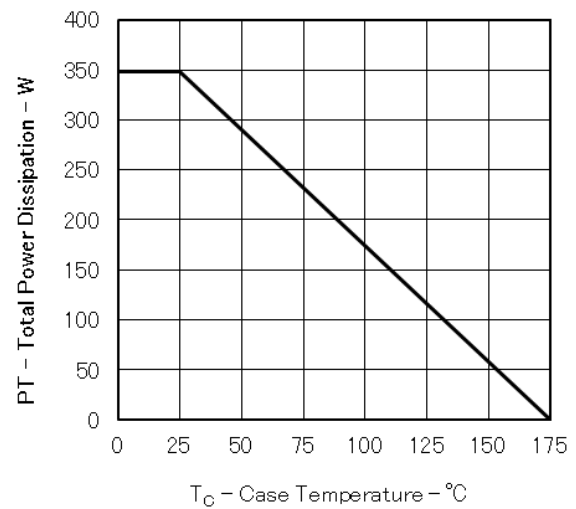


## Typical Characteristics

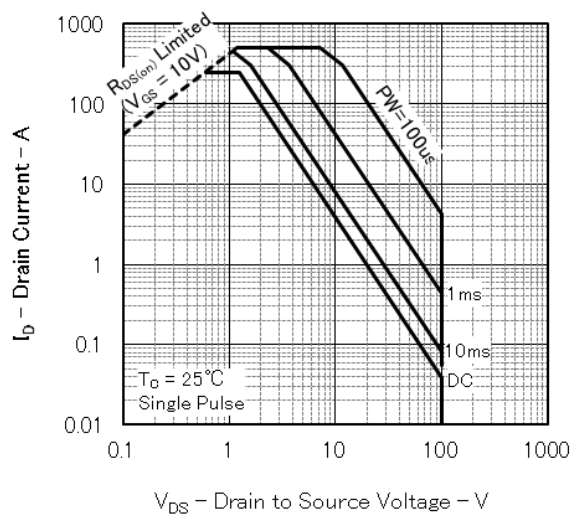
DERATING FACTOR OF FORWARD BIAS  
SAFE OPERATING AREA



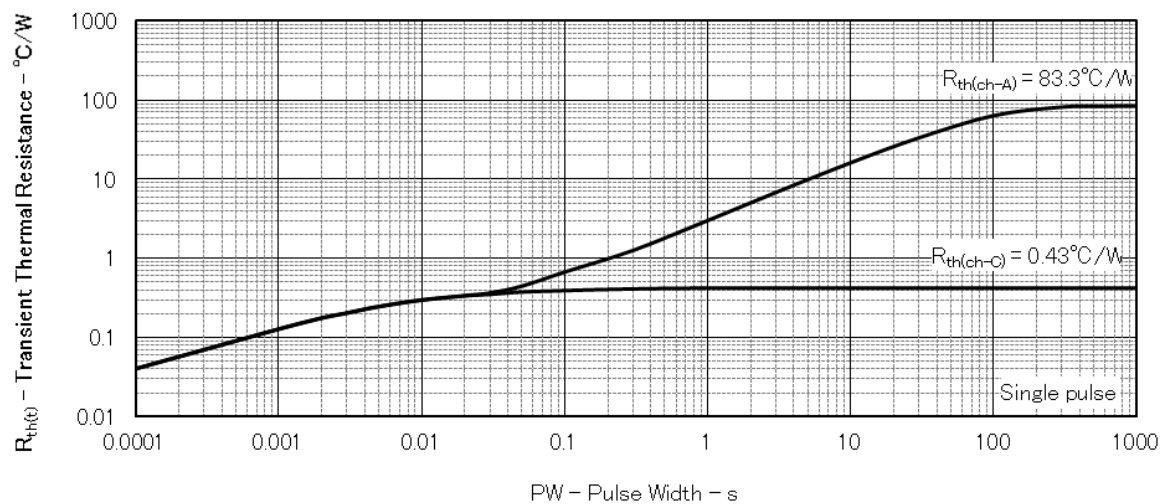
TOTAL POWER DISSIPATION vs.  
CASE TEMPERATURE

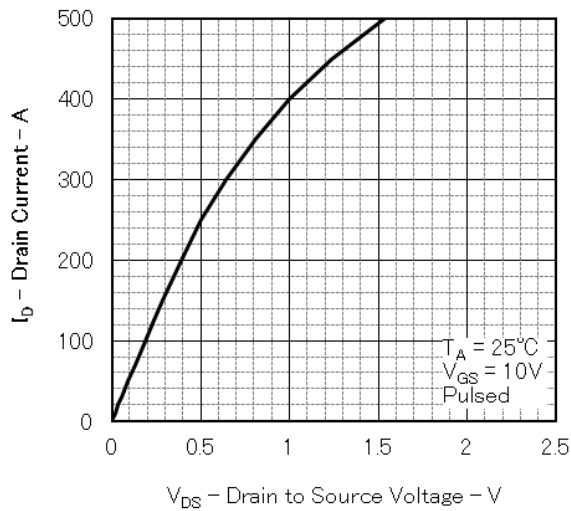


FORWARD BIAS SAFE OPERATING AREA

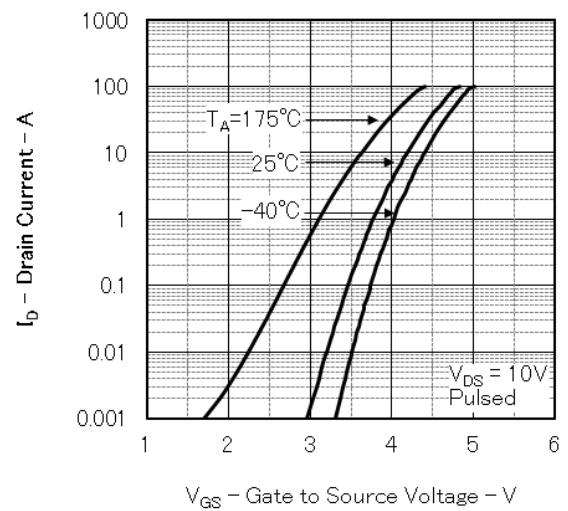
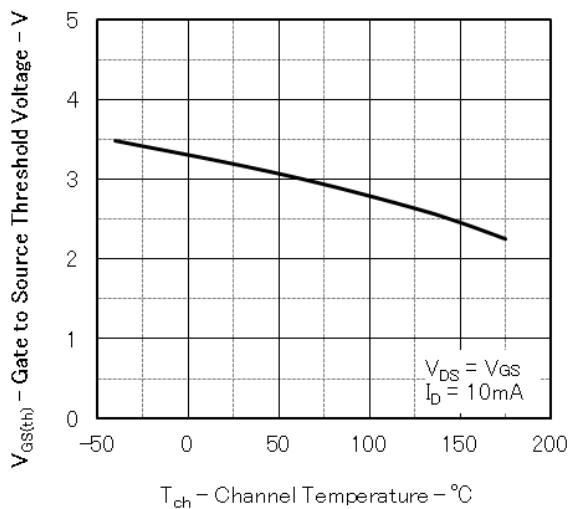
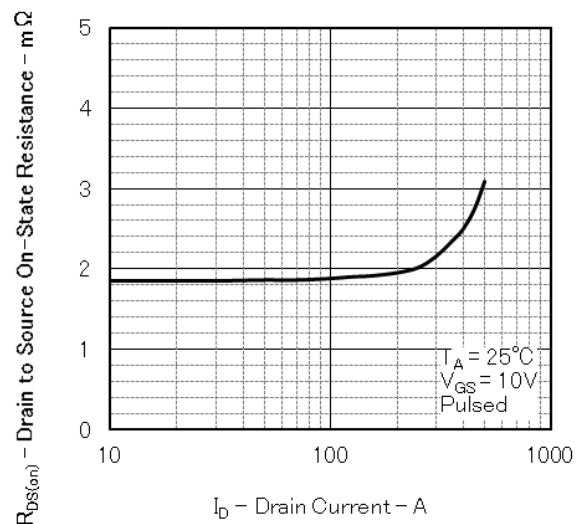
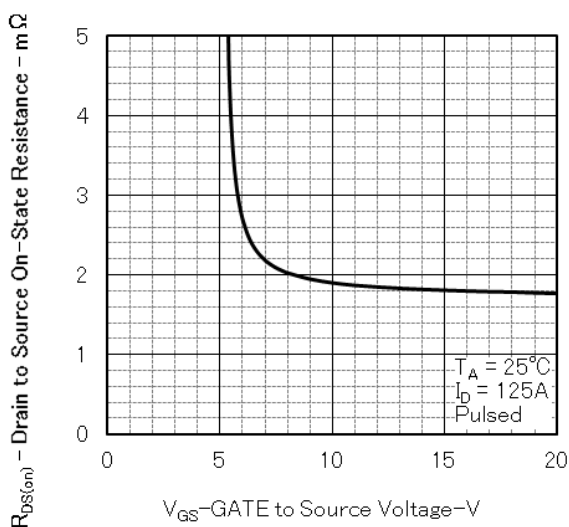
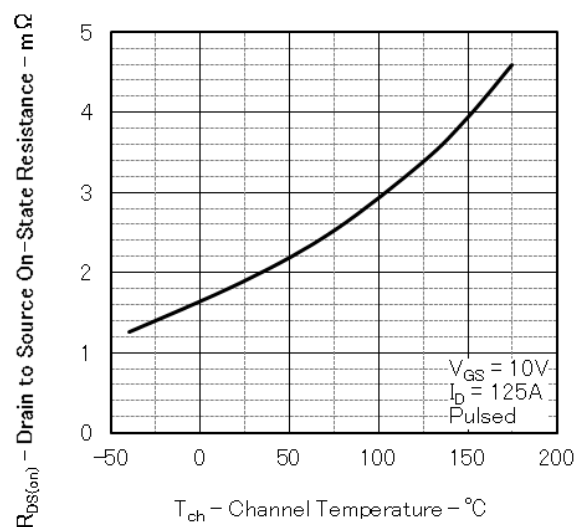


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

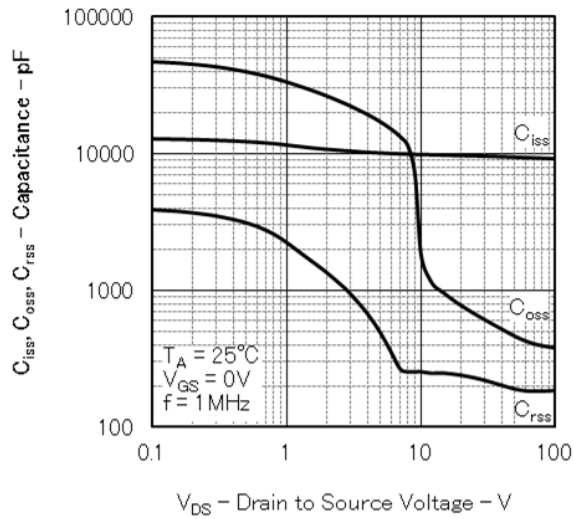


DRAIN CURRENT vs.  
DRAIN TO SOURCE VOLTAGE

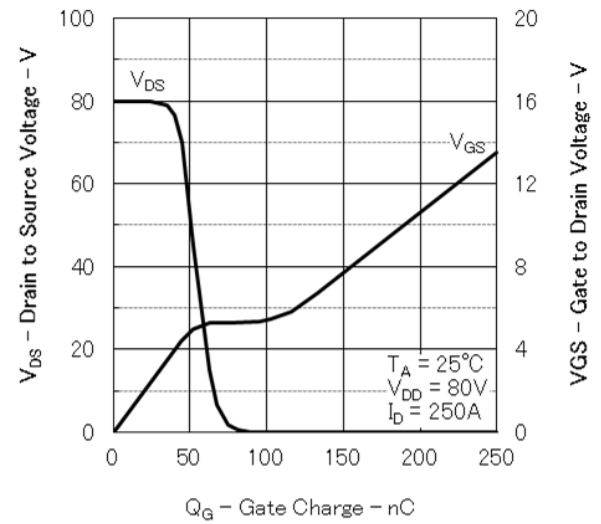
FORWARD TRANSFER CHARACTERISTICS

GATE TO SOURCE THRESHOLD VOLTAGE vs.  
CHANNEL TEMPERATUREDRAIN TO SOURCE ON-STATE  
RESISTANCE vs. DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.  
GATE TO SOURCE VOLTAGEDRAIN TO SOURCE ON-STATE RESISTANCE vs.  
CHANNEL TEMPERATURE

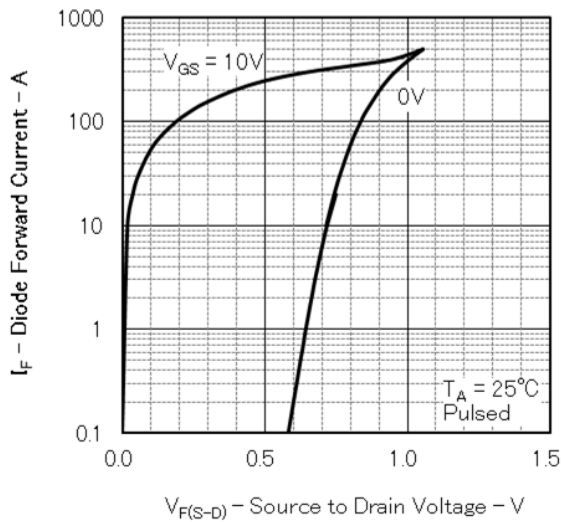
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



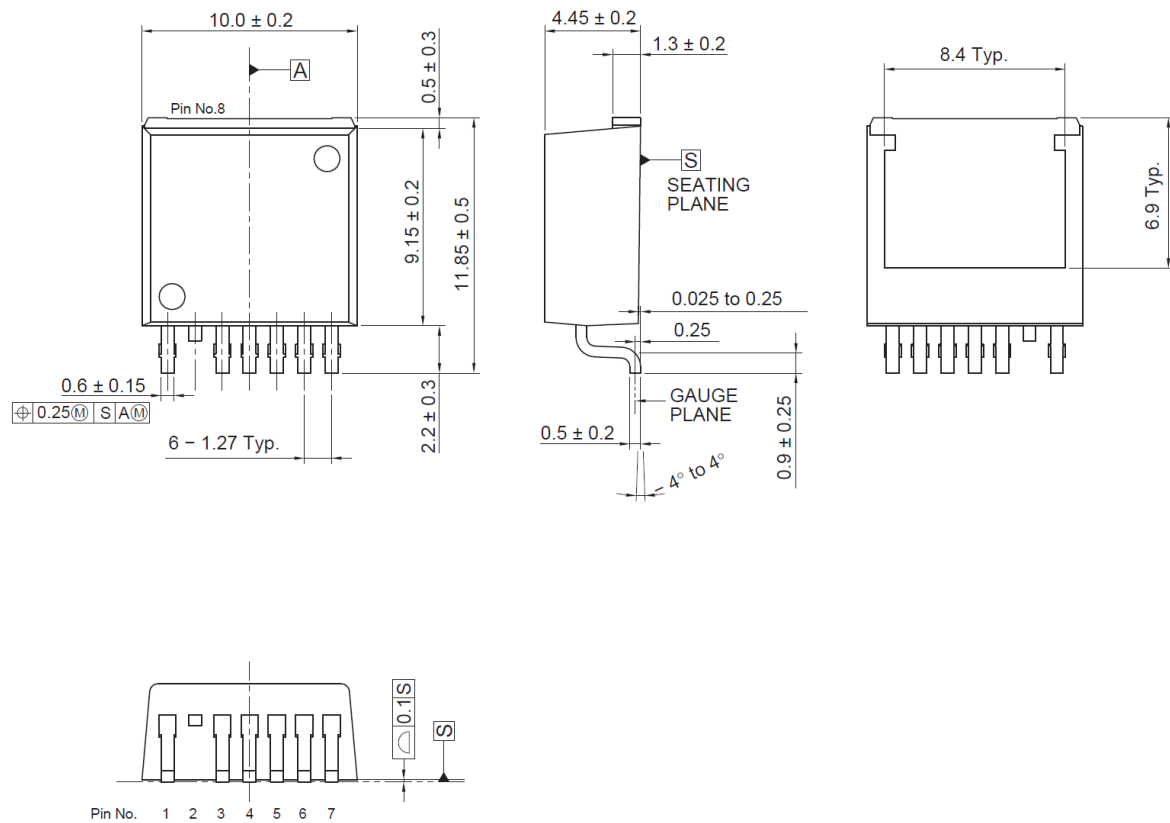
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



## Package Dimensions

| JEITA Package Code | RENESAS Code | Previous Code | MASS (Typ) [g] | Package Name |
|--------------------|--------------|---------------|----------------|--------------|
| —                  | PRSS0008DC-A | —             | 1.39           | MP-25ZU      |

Unit: mm



## Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
  2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
  3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
  4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
  5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.

"Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.

"High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
  6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
  7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
  8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
  9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
  10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
  11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
  12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)



### SALES OFFICES

### Renesas Electronics Corporation

<http://www.renesas.com>

Refer to "<http://www.renesas.com/>" for the latest and detailed information.

**Renesas Electronics Corporation**  
TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan

**Renesas Electronics America Inc.**  
1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.  
Tel: +1-408-432-8888, Fax: +1-408-434-5351

**Renesas Electronics Canada Limited**  
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3  
Tel: +1-905-237-2004

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
Room 101-T01, Floor 1, Building 7, Yard No. 7, 8th Street, Shangdi, Haidian District, Beijing 100085, China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai 200333, China  
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2265-6688, Fax: +852 2886-9022

**Renesas Electronics Taiwan Co., Ltd.**  
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan  
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

**Renesas Electronics Singapore Pte. Ltd.**  
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949  
Tel: +65-6213-0200, Fax: +65-6213-0300

**Renesas Electronics Malaysia Sdn.Bhd.**  
Unit No 3A-1 Level 3A Tower 8 UOA Business Park, No 1 Jalan Pengaturcara U1/51A, Seksyen U1, 40150 Shah Alam, Selangor, Malaysia  
Tel: +60-3-5022-1288, Fax: +60-3-5022-1290

**Renesas Electronics India Pvt. Ltd.**  
No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India  
Tel: +91-80-67208700

**Renesas Electronics Korea Co., Ltd.**  
17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea  
Tel: +82-2-558-3737, Fax: +82-2-558-5338